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Non linear Doping of Cuprate Superconductors – The case of $Bi_2Sr_{2-x}La_xCuO_{6+\delta}$

J. Röhler

Fachgruppe Physik, Universität zu Köln, Zülpicher Str.77, 50937 Köln, Germany

Abstract

We analyze the hole doping mechanism in $Bi_2Sr_{2-x}La_xCuO_{6+\delta}$ (BSLCO). The singular optimum around $x = 0.35$ is found to be connected with a feedback between the doped CuO_2 layers and its dopant reactant $[La^{3+}/Bi^{3+}–O_\delta]$ locking the number of doped holes preferentially on to the universal optimum $n_{opt} \simeq 0.16$.

Key words: hole doping, cuprate superconductors, overdoped, phase separation

The effective charge metallizing the CuO_2 layers in cuprate superconductors must be generated spatially outside in one of the functional layers or combinations of them, usually labelled “separating”, “insulating”, and ”spacing”. Thus the doping mechanism rendering cuprates superconducting is fundamentally different from that in high-T_c band metals, *e.g*. the superonducting iron pnictides. In the latter $3d$ transition metal or anion doping is reproducibly successfull, in the former it has an deterious effect on the superconductivity. By choosing which combinations of outside layers are used for dopant cations and/or oxygen atoms, T_c of the cuprates may be raised up to 160 K, three times higher than in high-T_c band suprconductors. Oxygen dopants, residing in the strongly polarizable “insulating” layers far apart from unbuckled CuO_2 sheets, were found to be most efficient enhancing T_c. The relationship between T_c and the number of carriers in p-type cuprate superconductors is universal in that T_c passes a common maximum at $n_{opt} = 0.16 \pm 0.01$, independent on the variety of the chemical and structural complexes hosting superconducting CuO_2 layers [1]. $1 - T_c/T_c^{max} = 82.6(n - 0.16)^2$ came into widespread use as “universal” parameterization of the the superconducting “dome” of hole doped cuprates. Truely universal, however, seems to be only the optimum hole number, $n_{opt} = 0.16$. The “domes” are generally distorted by striking dips (*e.g*. ubiquitously at $n = 1/8$), a cusp at the optimum, and by a strong asymmetry in the overdoped regime. And the nominal edges at the under- ($n = 0.05$) and overdoped ($n = 0.27$) sides are frequently found very close to the optimum, most prominently in La/Bi-doped BSLCO.

Superconductivity of BSLCO starts only at $n \geq 0.10$ and fades away already at $n \simeq 0.22$. A narrow asymmetric cusp in $T_c(n)$, unvariably centered at $n_{opt} = 0.16 \pm 0.01$ [2, 3], is unaffected by different crystal growth routes, varying Pb^{+3}/Bi^{+3} substitutions, and maxima ranging from 18 K in poly- to 34 K in monocrystalline samples. It is noteworthy that optimum doping maximizes not only T_c but also the volume fraction of the Meissner effect. Significant changes of the atomic structure occur at the optimum: the buckling of the CuO_2 layers gets minimized [4] and the symmetry of the superlattice cell uniformly orthorhombic, forcing out intergrown lamellae of underdoped monoclinic supercells [7]. Also the sharply peaking low-T Hall number exhibits singular behavior at $n_{opt} = 0.16$ [5]. Apparently the electronic and atomic structures of BSLCO lock on to the superconducting optimum. Noteworthy, the singular optimum is robust on a high energy scale. It is hard to reconcile it with a quantum critical point, and the rugged $T_c(n)$ relationship simply with the borderline of a quantum-critical fluctuation regime.

In this brief note we summarize a collaborative experimental effort [6] on BLSCO, bringing out that the doping mechanism to be non linear, not just linear charge transfer. The composition and the structure of the reactant doping optimally the CuO_2 layers, is itself constrained by the optimum $n_{opt} = 0.16$.

La^{3+}/Sr^{2+} substitution in BSCO is chemically correlated with the insertion of excess oxygen atoms into the “insulating” Bi^{3+}–O(3), and “separating” La^{3+}/Sr^{2+} layers. The excess oxygen atoms may reside at interstitial “A” and “B” sites, close to the octahedral apex (O3) and to the octahedral faces, respectively. La^{3+} bonds both, O^A and O^B, hence building an effective doping reactant: $[O^A\text{-}2La\text{-}O^B]_{0.5}$. BSLCO forms in the entire superconducting regime and is almost unaffected by post-annealing, a favorite system for experimentalists! O^A and O^B have different electronic functions. While O^A may oxidize the CuO_2 units to Cu^{III}, O^B may compensate just the La^{3+}/ Sr^{2+} charge contrast.

We model in Figs. 1,2 the relationship between the lanthanum concentration x and the total number of oxygen excess atoms, $\delta = \delta_{O^A} + \delta_{O^B}$, by a tilted “roof” (thick green lines). It peaks at $\delta = 0.33$ for $x = 0.33$, well within the experimentally established range of the optimum: $0.38 \geq x_{opt} \geq 0.3$. The peak postion is obtained from two intersecting straights: $\delta(x) = 0.5(1 - x)$ (not shown), and $\delta(x) = x$. The La-rich end member is insulating and antiferromagnetic, hence accomodates only $\delta = 0.5$ oxygen excess atoms in a non oxidizing

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Email address: `juergen.roehler@uni-koeln.de` (J. Röhler)
URL: `http://www.uni-koeln.de/~abb12` (J. Röhler)

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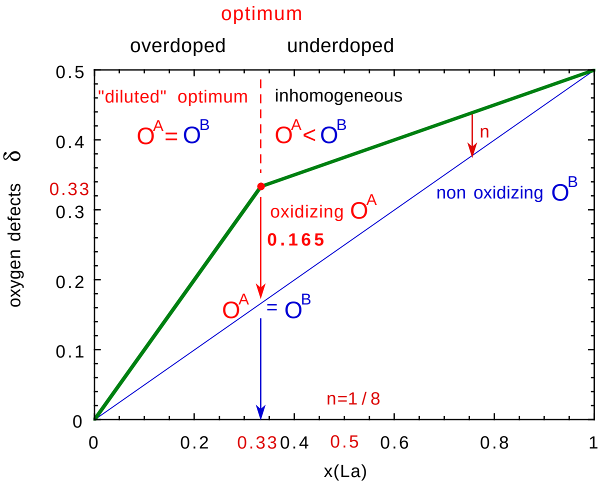

Figure 1: (color online) Number of oxygen excess atoms at interstitial A and B sites as a function of La in $Bi_2Sr_{2-x}La_xCuO_{6+\delta}$. O^B compensates the La/Sr charge contrast, O^A oxidizes the CuO_2 layers. Resulting hole numbers n are indicated by the vertical arrows. The universal optimum $n_{opt} \simeq 0.16$ occurs for $x = 0.33$. Note the paradoxial behavior in the overdoped regime $x \leq 0.33$.

$[2La\text{-}O^B]_{0.5}$ reactant. Removal of La^{3+} from the parent compound will nominally redistribute up to $\delta = 0.5$ oxygen excess atoms from B to oxidizing A sites in the reactant $[O^A\text{-}2La\text{-}O^B]_{0.5}$. In the La-poor regime however each added La^{3+} atom drags exactly one O^{2-} forming $[O^A\text{-}2La\text{-} O^B]_{0.5}$. Thus $\delta = x$ dopes optimally. The non oxidizing fraction follows the thin blue diagonal line. As indicated by the vertical red arrows in Fig. 1,2, $x_{opt} = 0.33$ dopes $n_{opt} = 0.165$ holes.

The left side of the "roof" is constructed assuming the nominal Bi^{3+} stoichiometry, leading to paradoxial "underdoping" in the overdoped regime $0 \leq x \leq 0.33$. But here $O^A = O^B$, in contrast to the underdoped regime. Alike the optimum with 0.165 holes for $x = 0.33$ the overdoped regime has $n = 0.5/x$. Notably all laboratories found excess nonstoichiometry of Bi to be mandatory for the safe growth of overdoped crystals. In fact, carefull examination of their actual stoichimetry brings out seizable excess of Bi^{3+}.

For $x \leq x_{opt}$ Bi^{3+} starts to substitute Sr^{2+} thereby expelling La^{3+}. The stoichiometry of overdoped BLSCO must be hence written $Bi_{2+y}Sr_{2-x-y}La_xCuO_{6+\delta}$. $y = \delta_0 - x$ may rise in La-free crystals up to 0.33. Dependent on the preparation T_c^{max} of $Bi_2Sr_{2-x}Bi_xCuO_{6+\delta}$ (BSBC) does not exceed $\simeq$ 10 K. Noteworthy, fully stoichiometric $Bi_2Sr_2CuO_6$, and $Bi_2Sr_2CuO_{6+\delta}$ decompose.

The special situation in the overdoped regime $0 \leq x_{opt} \leq 0.33$ is displayed in Fig. 2. Spectroscopically (by using XAS) the hole number in the overdoped regime was found to "saturate" [3], recently confirmed also from overdoped crystals of other cuprate families. Apparently the overdoped regime tends to reject all holes exceeding $n_{opt} \simeq 0.16$. As a consequence even the heavily doped system is in favor of the superconducting optimum. Chemical treatment attempting to force the system into the overdoped regime will only segregate the crystal into a phase mixture of optimum BSLCO with near optimum (or underdoped) BSBC. The mixed system gains the mixing ratio as additional thermodynamical degree of freedom stabilizing it with a constant hole number. Single crystal x-ray diffraction has recently found strong evidence for macroscopic decomposition in many overdoped crystals of BSLCO [7]. Fig. 2 proposes a simple lever rule to govern the actual mixing ratio (optimum BSLCO) : (optimum BSBCO) in the overdoped regime. Thus the total number of total number of oxygen excess atoms $\delta_{BSLCO} + \delta_{BSBCO} = 0.33$ is conserved in the entire overdoped regime. The hole number is fixed at $n_{opt} = 0.165$, note the vertical arrows in Fig. 2. Each of the two chemically different doping reactants is formed with equal amounts of O^A and O^B. Due to the lower T_c^{max} of BSBCO compared to BSLCO the effective T_c of the overdoped phase mixture however decreases.

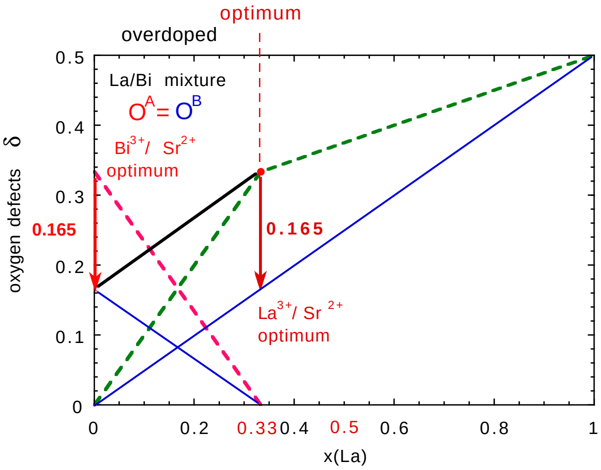

Figure 2: (color online) Analysis of the "hole saturation" (parallel thick lines) observed in the overdoped regime. Optimally doped CuO_2 layers are singular and tend to repell holes from overdoping [La-O] reactants. A lever rule governs the ratio of mixed BSBCO and BSLCO phases.

Clearly, the origin of the singular optimum at $n_{opt} = 0.16$ has to be sought in the special correlations between holes doped into CuO_2 layers [8]. But the doping reactant has to be able adapting to them by optimization of its effective structure through the optimally doped CuO_2 layers themselves.

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